

**IN THE ABSTRACT OF THE DISCLOSURE:**

Please amend the abstract as follows:

**ABSTRACT OF THE DISCLOSURE**

In a plasma processing method which comprises supplying a processing gas to a vacuum vessel 2-forming a plasma production part, producing a plasma 6-using an antenna 4-and a Faraday shield 8-which are provided at outer periphery of the vacuum vessel and to which a high-frequency electric power can be applied, and carrying out the processing, a voltage of at least 500 V is applied to the Faraday shield 8-and a sample 42-which is disposed in the vacuum vessel 2-and which is a nonvolatile material as a material to be etched is etched.